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## IN THE UNITED STATES PATENT &amp; TRADEMARK OFFICE

Appln. Ser. No.:	Filed:	Inventor(s):	Atty Dkt:
09/826,383	4 April 2001	S. Yoshida	114GI-143 (0694-143)

**Title: Electromagnetic Noise Suppressor, Semiconductor Device Using the Same, and Method of Manufacturing the Same**

**Examiner: Khiem Nguyen** **Art Unit: 2823**

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3 pages VIA FACSIMILE  
571-273-8300

## THIRD RESPONSE AFTER FINAL REJECTION

Dear Sir:

In supplement to the response filed yesterday, 19 October 2005, submitted is a graph of the  $\mu''_{\max}$  data from the examples of WO01054145A1, the publication of PCT/JP01/00437, referenced at page 17 of the present specification.

The graph shows the magnetic loss of the M-X-Y composition specifically recited in the claim ( $\mu''_{\max}$  – y-axis) versus the percentage saturation magnetization of the M-X-Y composition with respect to saturation magnetization of the M material alone ( $Ms(XYZ)/Ms(M)$  – x-axis). Graphically, the data indicate that a useful  $\mu''_{\max}$  occurs at a percent saturation magnetization of about 35 to about 80, as claimed.

As mentioned in the Second Response, filed yesterday, Inomata describes an active device wherein his compositions are disposed on the front side of the semiconductor device. In contrast, the claimed device comprises a "magnetic loss film" disposed on the "back" surface of device. Thus, Inomata does not anticipate the claims.

The present invention works by absorbing noise radiation and converting the noise to heat, thus the magnetic loss ( $\mu''_{\max}$ ) and other properties are important for shielding against radiation. Inomata makes no mention of these properties because that disclosure is directed to an active device wherein the granular layer forms part of two different tunnel junctions (see col. 10, ln. 6-12, and Fig. 4). It would not have been obvious from Inomata's use of a film as part of an active circuit disposed on the front side of a semiconductor device to use that film as a passive magnetic loss material on the back side of semiconductor device for absorbing radiation and being unconnected to any circuit..

Accordingly, the rejections should be withdrawn.

Respectfully submitted,



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20 October 2005

#### CERTIFICATE OF MAILING OR TRANSMISSION – 37 CFR 1.8

I hereby certify that I have a reasonable basis that this paper, along with any referred to above, (i) are being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450, or (ii) are being transmitted to the U.S. Patent & Trademark Office in accordance with 37 CFR § 1.6(d)

DATE: 20 October 2005

NAME: Brad Ruben

SIGNATURE: Brad Ruben

09/826,383

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